

Performance

- Technology: 0.25um Power GaN HEMT
- Frequency: 2.0~6.5GHz
- Typical Pout : $\geq 32\text{dBm(CW)}$
- Typical Gain: $\geq 17\text{dB}$
- Typical PAE: $\geq 35\%$
- Bias: 28V@0.2A
- Package: Metal Ceramic

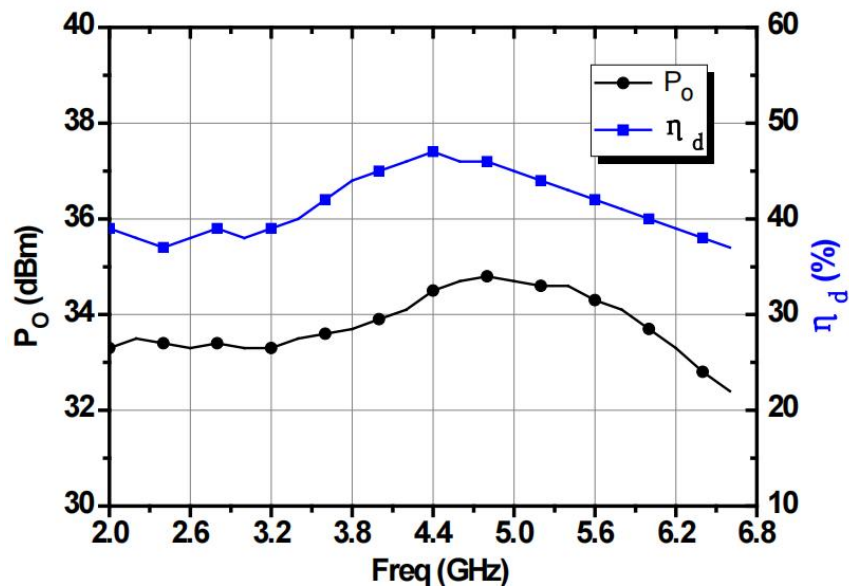


Electrical Specifications (TA=25°C,Vd=28V,Idq=0.2A,F: 2.0~6.5GHz,Pin=15dBm)

Symbol	Parameter	Min	Typical	Max	Unit
Pout	Output Power	32	-	-	dBm
Gp	Power Gain	17	-	-	dB
η_{add}	Power Added Efficiency	35	-	-	%
ΔG_p	Gain Flatness	-	-	± 1.2	dB

Test Curves

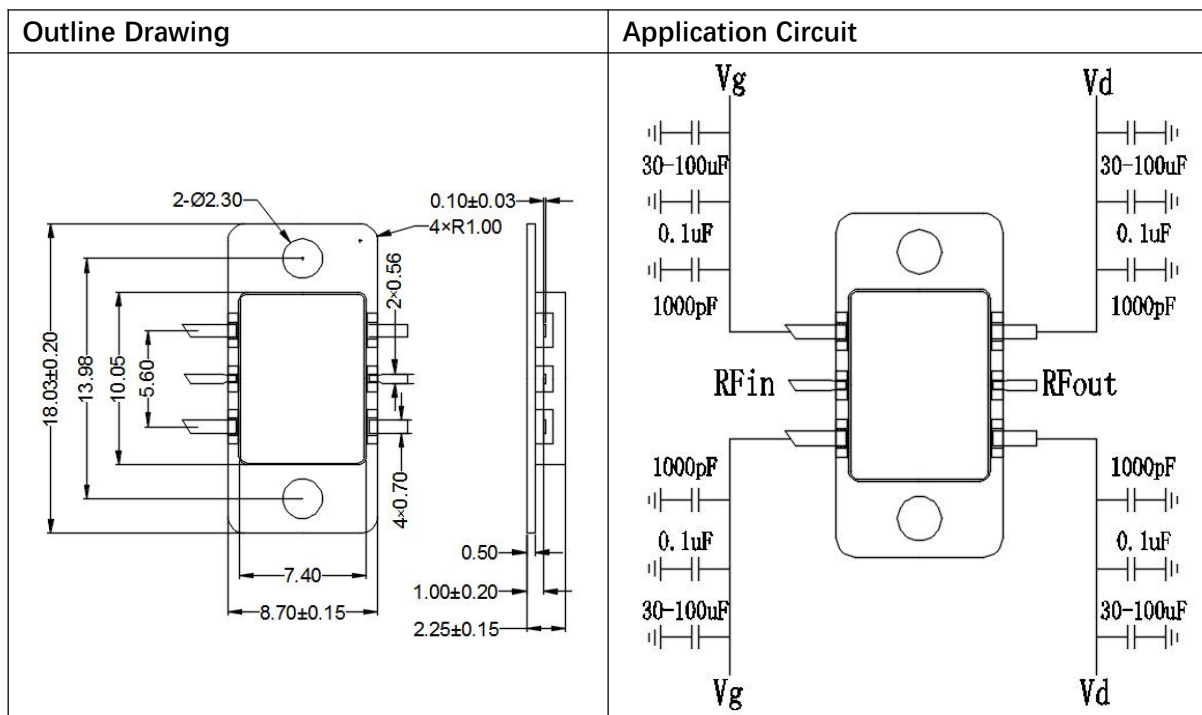
Pout、 η_d &Freq.



Absolute Max Ratings (T_A=25°C)

Symbol	Parameter	Value	Remark
V _d	Drain Voltage	32V	
V _g	Grid Voltage	-10V	
P _d	DC Dissipation	10W	
T _{ch}	Channel Temperature	225°C	【1】
T _m	Mounting Temperature	300°C	1 min, N ₂ Protection
T _{stg}	Storage Temperature	-55~175°C	

【1】 Exceeding any one or combination of these limits may cause permanent damage.



Note:

- (1) This product is an internal matching power amplifier module, with input and output impedance values of 50 ohms;
- (2) Please strictly follow the sequence of applying negative power first and then positive power. When removing power, first decrease the leakage voltage and then decrease the gate voltage;
- (3) This product is a high-power device, and attention should be paid to heat dissipation during use. The higher the shell temperature, the shorter the service life, and the appropriate use temperature should not be higher than 85 degrees Celsius;
- (4) This product is an electrostatic sensitive device, which requires attention to electrostatic protection during storage and use, and requires good grounding during use.